

CMXT2207

**SURFACE MOUNT
DUAL COMPLEMENTARY
SILICON TRANSISTORS**

SUPERmini™



SOT-26 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXT2207 type is a dual complementary silicon transistor manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, and designed for small signal general purpose and switching applications.

MARKING CODE: X07

MAXIMUM RATINGS: (T_A=25°C)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Continuous Collector Current
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL	NPN		PNP		UNITS
V _{CBO}	75		60		V
V _{CEO}	40		60		V
V _{EBO}	6.0		5.0		V
I _C		600			mA
P _D		350			mW
T _J , T _{stg}		-65 to +150			°C
θ _{JA}		357			°C/W

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
I _{CBO}	V _{CB} =60V	-	10	-	-	nA
I _{CBO}	V _{CB} =50V	-	-	-	10	nA
I _{CBO}	V _{CB} =60V, T _A =125°C	-	10	-	-	µA
I _{CBO}	V _{CB} =50V, T _A =125°C	-	-	-	10	µA
I _{EBO}	V _{EB} =3.0V	-	10	-	-	nA
I _{CEV}	V _{CE} =60V, V _{EB} =3.0V	-	10	-	-	nA
I _{CEV}	V _{CE} =30V, V _{BE} =0.5V	-	-	-	50	nA
BV _{CBO}	I _C =10µA	75	-	60	-	V
BV _{CEO}	I _C =10mA	40	-	60	-	V
BV _{EBO}	I _E =10µA	6.0	-	5.0	-	V
V _{CE(SAT)}	I _C =150mA, I _B =15mA	-	0.3	-	0.4	V
V _{CE(SAT)}	I _C =500mA, I _B =50mA	-	1.0	-	1.6	V
V _{BE(SAT)}	I _C =150mA, I _B =15mA	0.6	1.2	-	1.3	V
V _{BE(SAT)}	I _C =500mA, I _B =50mA	-	2.0	-	2.6	V
h _{FE}	V _{CE} =10V, I _C =0.1mA	35	-	75	-	
h _{FE}	V _{CE} =10V, I _C =1.0mA	50	-	100	-	
h _{FE}	V _{CE} =10V, I _C =10mA	75	-	100	-	
h _{FE}	V _{CE} =10V, I _C =150mA	100	300	100	300	
h _{FE}	V _{CE} =1.0V, I _C =150mA	50	-	-	-	
h _{FE}	V _{CE} =10V, I _C =500mA	40	-	50	-	
f _T	V _{CE} =20V, I _C =20mA, f=100MHz	300	-	-	-	MHz
f _T	V _{CE} =20V, I _C =50mA, f=100MHz	-	-	200	-	MHz

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CMXT2207

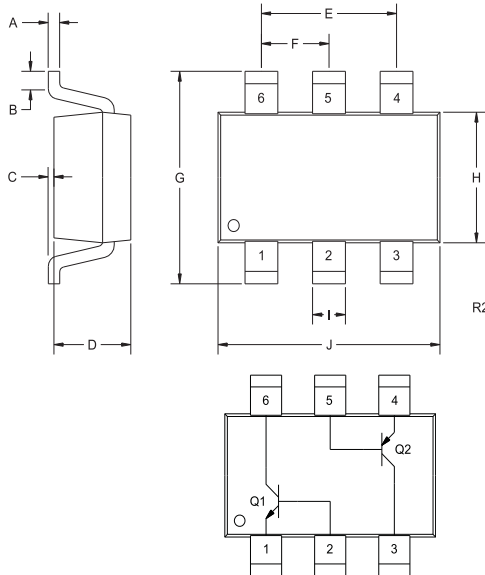
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	NPN		PNP		UNITS
		MIN	MAX	MIN	MAX	
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$	-	8.0	-	8.0	pF
C_{ib}	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$	-	25	-	-	pF
C_{ib}	$V_{EB}=2.0\text{V}, I_C=0, f=1.0\text{MHz}$	-	-	-	30	pF
h_{ie}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	2.0	8.0	-	-	k Ω
h_{ie}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	0.25	1.25	-	-	k Ω
h_{re}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	-	8.0	-	-	$\times 10^{-4}$
h_{re}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	-	4.0	-	-	$\times 10^{-4}$
h_{fe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	50	300	-	-	
h_{fe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	75	375	-	-	
h_{oe}	$V_{CE}=10\text{V}, I_C=1.0\text{mA}, f=1.0\text{kHz}$	5.0	35	-	-	μS
h_{oe}	$V_{CE}=10\text{V}, I_C=10\text{mA}, f=1.0\text{kHz}$	25	200	-	-	μS
$rb'C_c$	$V_{CB}=10\text{V}, I_E=20\text{mA}, f=31.8\text{MHz}$	-	150	-	-	ps
NF	$V_{CE}=10\text{V}, I_C=100\text{mA}, R_S=1.0\text{k}\Omega, f=1.0\text{kHz}$	-	4.0	-	-	dB
t_{on}	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	-	-	45	ns
t_d	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	10	-	10	ns
t_r	$V_{CC}=30\text{V}, V_{BE}=0.5\text{V}, I_C=150\text{mA}, I_{B1}=15\text{mA}$	-	25	-	40	ns
t_{off}	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	100	ns
t_s	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	225	-	-	ns
t_s	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	80	ns
t_f	$V_{CC}=30\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	60	-	-	ns
t_f	$V_{CC}=6.0\text{V}, I_C=150\text{mA}, I_{B1}=I_{B2}=15\text{mA}$	-	-	-	30	ns

SOT-26 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016	-	0.41	-
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Emitter Q1
- 2) Base Q1
- 3) Collector Q2
- 4) Emitter Q2
- 5) Base Q2
- 6) Collector Q1

MARKING CODE: X07

R3 (12-February 2010)

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

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